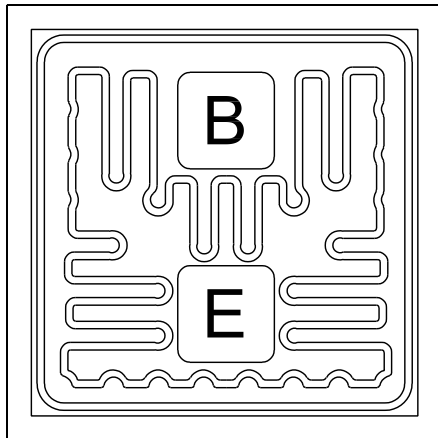


PROCESS DETAILS

Process	Epitaxial Planar
Die Size	18 x 18 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.8 x 3.8 MILS
Emitter Bonding Pad Area	3.8 x 3.8 MILS
Top Side Metalization	Al/Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

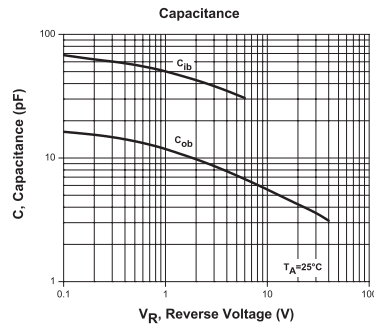
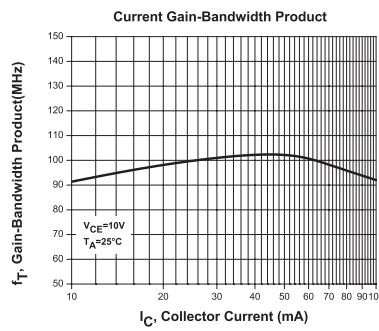
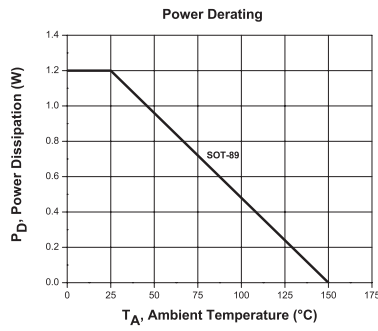
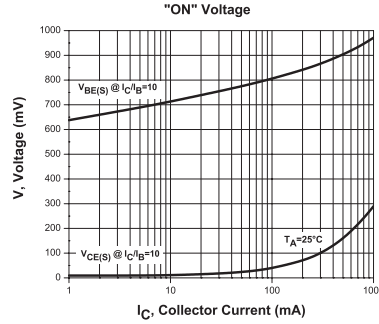
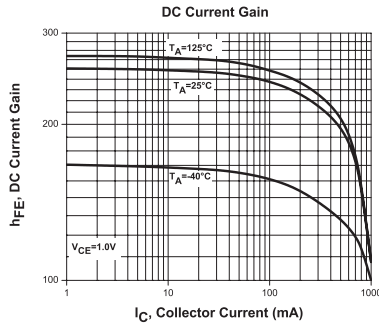
54,330

PRINCIPAL DEVICE TYPES

CMLT3410
CMPT3410
CMST3410
CMUT3410
CXT3410

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R1 (10- April 2007)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R1 (10- April 2007)